Physical properties of polyacetylene films doped with MoCl₅ and WCl₆

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The physical properties of polyacetylene $(CH)_x$ are considerably modified by doping with halogens (*p* type) or alkalis (*n* type). In this paper we present the effects of new kinds of dopants — salts of transition metals such as WCI₆ and MoCl₅. Dopant diffusion inside the film, the electrical behaviour and the infra-red transmission are studied and compared with effects produced by usual dopants. They have low diffusion coefficients and readily produce large dopant concentration using salt solutions.

Keywords Polymer; polyacetylene; spectroscopy; conductivity; doping; profiles

INTRODUCTION

Polyacetylene (CH)_x, the simplest conjugated polymeric system available as flexible films, is an extensively studied material. Its physical properties are considerably modified by a doping process, particularly its electrical and optical behaviour. A number of *n* and *p* type dopants have now been discovered^{1,2} and their influence on the polymer pointed out³. In this paper we study the effect of new dopants of polyacetylene; derivatives of transition metals. In a recent paper⁴ we showed that MoCl₅ and WCl₆ are catalytic systems for the polymerization of C_2H_2 . We also pointed out that the polymers so prepared showed greater conductivity than those obtained with the usual catalysts Ti(OBu)₄-l(Et)₃.

From this we realize the (CH)_x doping with MoCl₅ and WCl₆ and then study the dopant diffusion in the polymer, the behaviour of the electrical conductivity and infra-red transmission *versus* the dopant concentration. The results are compared with those already known. The main point lies in the fact that their diffusion coefficients in (CH)_x are lower than those of previous dopants, their stability is higher and a large range of dopant concentrations may be easily obtained and controlled.

EXPERIMENTAL

Polyacetylene films were prepared by the Shirakawa's technique using the catalytic system $Al(Et)_3$ -Ti(OBu)₄ in toluene at -78°C in order to obtain the *cis* isomer. Sample thicknesses were: 150 μ m for the Castaing microprobe analysis and electrical conductivity measurements, 50 μ m for the visible study. In the latter case the film thickness is measured by mean of scanning electron microscopy. The samples were doped using a solution of MoCl₅ or WCl₆ in toluene; various concentrations being used, ranging from a saturated solution (S) down to a 10⁻² S solution. When thick films (150 μ m) are used the dopant content is measured by weight uptake, but for the infra-red measurements the

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doping is too light to be measured by weight uptake and the dopant content is related to the doping time in a solution. Finally we used very thin films ($\simeq 0.1 \ \mu m$) directly polymerized onto a glass substrate for the visible transmission, where even a high doping level cannot be measured.

Dopant profiles through the samples were measured by means of Castaing microprobe analysis (CAMECA MS 46 type apparatus), the detailed experimental procedure being described in an earlier publication⁵. Electrical conductivity was studied from 77K up to 300K for a large range of dopant concentration $(10^{-3} < y < 10^{-1})$ in the formula $[CH(WCl_6)_y]_x$ or $[CH(MoCl_5)_y]_x$; measurements were performed by the usual four probe technique, gold wires being fastened with electrodag paste. Middle infrared transmission measurements were performed with a Perkin Elmer 577 spectrophotometer and a visible study on a Beckman Acta M IV apparatus.

RESULTS

Dopant profiles

Figure 1 shows typical dopant profile (W in WCl_{4}) through a 150 μ m thick sample. Firstly we notice a strong dopant gradient between the surface (high concentration) and the middle (low and even null concentration) which proves the non-uniformity of the dopant concentration. Secondly a non-symmetry appears in this profile; this effect can easily be related to the difference in the (CH), films morphology surfaces. On Figure 2 we have reported various dopant profiles of W obtained after various doping times in a saturated solution of WCl₆ (the films are characterized both by the doping time and the mean value y of dopant content). We observe that a very long doping time is necessary to obtain an almost uniform dopant concentration ($t = 6 \times 10^5$ s). This leads to a relatively dopant diffusion coefficient which small can approximately be estimated to 10^{-10} cm² s⁻¹ (compared to the iodine diffusion $D \simeq 10^{-7} \text{ cm}^2 \text{ s}^{-1}$).



Figure 1 W profiles through WCl₆ doped $(CH)_X$ films: (a) $[CH(WCl_6)_{0.003}]_X$; (b) $[CH(WCl_6)_{0.013}]_X$



Figure 2 W profiles through WCl₆ doped polyacetylene for a large doping time (t) range: (t = 10'', y = 0.0015, t = 30'', y = 0.003, t = 100'', y = 0.007, t = 300'', y = 0.013, t = 20000'', y = 0.035, t = 600 000'', y = 0.10)

Electrical conductivity

The maximum conductivity, obtained for y=0.1 in both cases, lies around $\sigma \simeq 200 \ \Omega^{-1} \ \mathrm{cm}^{-1}$. Figure 3 shows that the dopant concentration dependence of the conductivity is quite similar to those obtained with usual dopants. Figures 4 and 5 respectively, exhibit the electrical resistivity variations of MoCl₅ and WCl₆ doped (CH)_x films, versus $10^3/T$.

A semiconducting behaviour is observed—the dependence is not linear particularly at low temperatures—however we can deduce (at high temperatures) an activation energy which decreases strongly when dopant concentration increases reaching about 8 8 meV for $[CH(MoCl_5)_{0.1}]_x$ (the results are reported in *Figure 6*).

Middle infra-red and visible transmission

Figure 7 shows a series of transmission through a 50 μ m thick film for various doping times, i.e. at various (increasing) dopant concentrations of MoCl₅. A strong, but narrow, absorption appears at 1380 cm⁻¹ where the transmission becomes rapidly negliglible, and a broad absorption band lies between 850 and 950 cm⁻¹. The other bands appearing at 1720 and 1680 cm⁻¹ are attributed to the film oxidation. Similar results were



Figure 3 Electrical conductivity versus dopant concentrations. (+) CF_3SO_3H ; (\bullet) SbF_5 ; (\triangle) WCI_6 ; (\bigcirc) $MoCI_5$



Figure 4 Electrical resistivity of $[CH(MoCl_5)_y]_X$ samples versus $10^3/T$ for various dopant concentrations y.

obtained with WCl_5 doped samples in which case (vacuum performed experiments) we verified that the 1720 cm⁻¹ and 1680 cm⁻¹ bands do not appear.

However, the 450 cm⁻¹ band (*cis* isomer band) decreases slightly when the dopant concentration increases; this indicates a light *cis-trans* isomerization induced by doping. It appears that a much higher dopant concentration is necessary to produce further isomerization of the polymer. Note that the *cis-trans* isomerization also appears on the 3010 cm⁻¹ (*trans*) and 3050 cm⁻¹ (*cis*). The additional absorption over the undoped sample is reported in *Figure 8* where we observe excess absorption coefficients around 0.11 eV and at 0.173 eV (the excess absorption near 0.195 eV may be attributed to the film oxidation). Finally we used infra-red



Figure 5 Electrical resistivity of $[CH(WCI_6)_Y]_X$ samples versus $10^3/T$ for various y values

measurements in order to study the polyacetylene evolution during the dopant desorption process. Data are reported in Figure 9 where: curve (1) corresponds to the undoped cis rich (CH)_x film (65 μ m thick), curve (2) to the lightly MoCl, doped film and curves (3), (4) to the same film respectively wetted in toluene during 20 minutes and 850 minutes in order to obtain a dopant desorption. We mainly observe: an increase of the transmission over the whole range studied and especially near 1380 cm⁻¹ and $900 \,\mathrm{cm}^{-1}$, that is to say in the absorption bands due to the dopant. However the effect of the dopant on the absorption bands of the cis and trans isomers are not reversible and we chiefly observe this effect on the (450, 750 and 3050 cm^{-1}) cis bands whose intensities are reduced by the doping; while the 1000 cm^{-1} trans band is enhanced.

Near infra-red and visible transmissions were measured on very thin films ($\simeq 1000$ Å thick) directly polymerized onto a glass substrate. The film was doped in a saturated MoCl₅ solution in toluene for various times. From these measurements the evolutions of the absorption coefficient *versus* photon energy for various dopant concentrations are plotted in *Figure 10*. We notice a double maximum around 1.9 and 2.1 eV which persists even at high dopant levels; however, another maximum of the absorption coefficient increases during the doping process in all the range (1–3 eV) between 10⁵ and 3 × 10⁵ cm⁻¹. Finally we



Figure 6 Dopant concentration dependence of electrical activation energy in (CH)_X film. (+) CF₃SO₃H; (\bullet) SbF₃; (\triangle) WCl₆; (\bigcirc) MoCl₅



Figure 7 Middle infra-red transmission of light MoCl₅ doped (CH)_x film at various dopant stages



Figure 8 Additional absorption (over undoped samples) deduced from *Figure 7* results



Figure 9 Middle infra-red transmission at various dopant (MoCl₅) desorption stages

must notice that, in such a thin film some inhomogeneities can exist in the film thickness ($\simeq 0.1 \ \mu$ m). Therefore we assume a general evolution of the absorption coefficient more than its absolute value.

DISCUSSION

First the microprobe analysis of the dopant profiles shows that there is a dopant inhomogeneity through the sample thickness due to the dopant diffusion; but as the surface concentration greatly increases with the doping time, and also from the discrepancy between the observed profiles and the usual erf functions, obtained from Fick's Laws we can deduce that the diffusion is not the only effect observed but that a physical adsorption of dopant molecules also takes place on the polymer fibrils; this result was pointed out elsewhere⁶. An advantage of WCl₆ is its low diffusion coefficient $(D \simeq 10^{-10} \text{ cm}^2 \text{ s}^{-1})^8$ (results obtained with MoCl₅ and other transition metals seem to be similar). From those first results we can expect that those salts may be more stable dopants than those already known.

The effect of WCl₆ and MoCl₅ on the electrical conductivity of $(CH)_x$ films is quite similar to those obtained with iodine or SbF₅⁹: a large increase in conductivity (12 orders of magnitude) is observed, especially between y=0 and y=0.01, and the deduced activation energy exhibits a semiconductor to metal transition around $y \simeq 10^{-2}$. The departure from the straight line in the curves $\text{Log } \rho = f\left(\frac{10^3}{T}\right)$ at low

temperatures is larger than those observed with SbF₅ dopant, and with I₂ or CF₃SO₃H this effect is relatively negligible: if we compare the diffusion coefficient of such dopants we observe that $D_{CF_3SO_3H} \simeq D_{I_2} > D_{SbF_3} > D_{WCI_3}$. Therefore the gradient of dopant concentration through the sample increases when D decreases and at low temperatures the thin high doped surface sides produce a more conductive part than the thick low doped central part of the sample. Such an effect could explain the nonlinear behaviour observed at low temperatures and dopant concentrations. Concerning the optical properties the effects already observed¹⁰ with the 'usual dopants' appear here, for the middle infra-red transmission as well as for the visible transmission and particularly the narrow band at 1380 cm^{-1} and the broad band around 850 cm^{-1} . We note the *cis-trans* isomerization induced by doping; however this effect seems to be small on these lightly doped samples and it might be interesting to study the evolution of the cis to trans ratio versus the dopant concentration.

The desorption experiments showed the reversibility of the middle infra-red transmission in all the range except for the parts concerning the polyacetylene bands, giving a confirmation of the non-reversibility of the *cis-trans* isomerization.

CONCLUSION

We reported the first results concerning polyacetylene films doped with transition metal salts as WCl_6 and $MoCl_5$, and showed that all the studied properties such as the electrical conductivity, infra-red and visible absorptions presented similar behaviour to the usual dopants of this polymer; however it seems that this study, which must be extended to the other transition metal salts, has given some interesting results.

These dopants make it possible to obtain easily a very large range of dopant concentrations, especially for low doping levels, by using dilute solutions. Their low diffusion coefficients allow us to obtain more stable systems. Finally it seems that all 'dopants' of (CH), lead to



Figure 10 Near infra-red and visible absorption coefficient of undoped and MoCl_5 doped (CH)_X film

quite identical effects on its physical properties and we think that the knowledge of the largest possible number of polyacetylene dopants may be of some interest in order to understand the physical part played by these species on the polymer.

ACKNOWLEDGEMENT

Financial support from DRET under contract No. 78/1259 is gratefully acknowledged.

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